

National Semiconductor

February 1995

DS55451/2/3/4, DS75451/2/3/4 Series **Dual Peripheral Drivers**

General Description

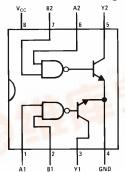
The DS7545X series of dual peripheral drivers is a family of versatile devices designed for use in systems that use TTL logic. Typical applications include high speed logic buffers, power drivers, relay drivers, lamp drivers, MOS drivers, bus drivers and memory drivers.

The DS55451/DS75451, DS55452/DS75452, DS55453/ DS75453 and DS55454/DS75454 are dual peripheral AND, NAND, OR and NOR drivers, respectively, (positive logic) with the output of the logic gates internally connected to the bases of the NPN output transistors.

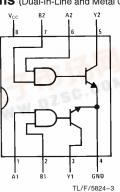
Features

- 300 mA output current capability
- High voltage outputs
- No output latch-up at 20V
- High speed switching
- Choice of logic function
- TTL compatible diode-clamped inputs
- Standard supply voltages
- Replaces TI "A" and "B" series

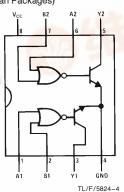
Connection Diagrams (Dual-In-Line and Metal Can Packages)



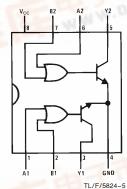
TL/F/5824-2 **Top View** Order Number DS55451J-8, DS75451M or DS75451N



Top View DS75452M or DS75452N



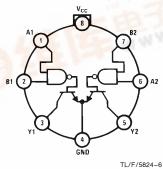
Top View Order Number DS55452J-8, Order Number DS55453J-8, Order Number DS55454J-8, DS75453M or DS75453N



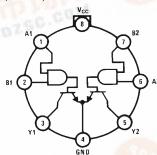
Top View DS75454M or DS75454N

See NS Package Numbers J08A, M08A* or N08E

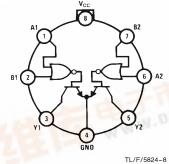
*See Note 5 and Appendix E regarding S.O. package power dissipation constraints.



Top View



TL/F/5824-7 **Top View**



Top View

Order Number DS55451H

Order Number DS55452H

(Pin 4 is in Electrical Contact with the Case) Order Number DS55453H

See NS Package Number H08C

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Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage, (V _{CC}) (Note 2)	7.0V
Input Voltage	5.5V
Inter-Emitter Voltage (Note 3)	5.5V
Output Voltage (Note 4)	
DS55451/DS75451, DS55452/DS75452,	30V
DS55453/DS75453, DS55454/DS75454	
Output Current (Note 5)	

DS55451/DS75451, DS55452/DS75452, 300 mA DS55453/DS75453, DS55454/DS75454

DS75451/2/3/4 Maximum Power (Note 5)

Dissipation† at 25°C

 Cavity Package
 1090 mW

 Molded DIP Package
 957 mW

 TO-5 Package
 760 mW

 SO Package
 632 mW

Storage Temperature Range -65°C to $+150^{\circ}\text{C}$ Lead Temperature (Soldering, 4 sec.) 260°C

Operating Conditions

	Min	Max	Units
Supply Voltage, (V _{CC})			
DS5545X	4.5	5.5	V
DS7545X	4.75	5.25	V
Temperature, (T _A)			
DS5545X	-55	+ 125	°C
DS7545X	0	+70	°C

[†] Derate cavity package 7.3 mW/°C above 25°C; derate molded package 7.7 mW/°C above 25°C; derate TO-5 package 5.1 mW/°C above 25°C; derate SO package 7.56 mW/°C above 25°C.

Electrical Characteristics

DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454 (Notes 6 and 7)

Symbol	Parameter		Conditions			Min	Тур	Max	Units
V _{IH}	High-Level Input Voltage	(Figure 7)	(Figure 7)			2			V
V _{IL}	Low-Level Input Voltage							0.8	V
VI	Input Clamp Voltage	V _{CC} = Min, I	_I = −12 mA					-1.5	V
V _{OL}	Low-Level Output Voltage	$V_{CC} = Min,$	$V_{IL} = 0.8V$	I _{OL} = 100 mA	DS55451, DS55453		0.25	0.5	٧
		(Figure 7)			DS75451, DS75453		0.25	0.4	٧
				I _{OL} = 300 mA	DS55451, DS55453		0.5	0.8	٧
					DS75451, DS75453		0.5	0.7	٧
			$V_{IH} = 2V$	I _{OL} = 100 mA	DS55452, DS55454		0.25	0.5	٧
					DS75452, DS75454		0.25	0.4	٧
				$I_{OL} = 300 \text{ mA}$	DS55452, DS55454		0.5	0.8	٧
					DS75452, DS75454		0.5	0.7	٧
I _{OH}	High-Level Output Current	$V_{CC} = Min,$	$V_{OH} = 30V$	H = 30V V _{IH} = 2V	DS55451, DS55453			300	μΑ
		(Figure 7)			DS75451, DS75453			100	μΑ
				$V_{IL} = 0.8V$	DS55452, DS55454			300	μΑ
					DS75452, DS75454			100	μΑ
lı	Input Current at Maximum Input Voltage	$V_{CC} = Max,$	V _{CC} = Max, V _I = 5.5V, (<i>Figure 9</i>)					1	mA
I _{IH}	High-Level Input Current	V _{CC} = Max,	$V_1 = 2.4V, (F_1)$	igure 9)				40	μΑ
I _{IL}	Low-Level Input Current	V _{CC} = Max,	$V_{\parallel} = 0.4V$, (Fi	igure 8)			-1	-1.6	mA
Іссн	Supply Current, Outputs High	V _{CC} = Max,	$V_I = 5V$		DS55451/DS75451		7	11	mA
		(Figure 10)	$V_I = 0V$		DS55452/DS75452		11	14	mA
			$V_I = 5V$		DS55453/DS75453		8	11	mA
			$V_I = 0V$		DS55454/DS75454		13	17	mA
ICCL	Supply Current, Outputs Low	V _{CC} = Max,	Max, $V_I = 0V$ DS55451/D		DS55451/DS75451		52	65	mA
		(Figure 10)	$V_I = 5V$		DS55452/DS75452		56	71	mA
			$V_I = 0V$ DSS		DS55453/DS75453		54	68	mA
			$V_I = 5V$		DS55454/DS75454		61	79	mA

Switching Characteristics

DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454 ($V_{CC}=5V, T_A=25^{\circ}C$)

Symbol	Parameter	Condition	ons	Min	Тур	Max	Units
t _{PLH}	Propagation Delay Time, Low-to-High	- ' - '	DS55451/DS75451		18	25	ns
	Level Output	$I_0 \approx 200 \text{ mA}, (Figure 14)$	DS55452/DS75452		26	35	ns
			DS55453/DS75453		18	25	ns
			DS55454/DS75454		27	35	ns
t _{PHL}	Propagation Delay Time, High-to-Low		DS55451/DS75451		18	25	ns
	Level Output	$I_0 \approx 200 \text{ mA}, (Figure 14)$	DS55452/DS75452		24	35	ns
			DS55453/DS75453		16	25	ns
			DS55454/DS75454		24	35	ns
t _{TLH}	Transition Time, Low-to-High Level Output	$C_L = 15 pF, R_L = 50 \Omega, I_O \approx 200 mA,$ (Figure 14)			5	8	ns
t _{THL}	Transition Time, High-to-Low Level Output	$\rm C_L=15pF,R_L=50\Omega,I_O\approx200mA,$ (Figure 14)			7	12	ns
V _{OH}	High-Level Output Voltage after Switching	$V_S = 20V$, $I_O \approx 300$ mA, (Figure 15)		V _S - 6.5			mV

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Voltage values are with respect to network ground terminal unless otherwise specified.

 $\textbf{Note 3:} \ \ \textbf{The voltage between two emitters of a multiple-emitter transistor.}$

Note 4: The maximum voltage which should be applied to any output when it is in the "OFF" state.

Note 5: Both halves of these dual circuits may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation rating.

Note 6: Unless otherwise specified min/max limits apply across the -55° C to $+125^{\circ}$ C temperature range for the DS55450 series and across the 0° C to $+70^{\circ}$ C range for the DS7545X series. All typicals are given for $V_{CC} = +5V$ and $T_A = 25^{\circ}$ C.

Note 7: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Truth Tables (H = high level, L = low level)

DS55451/DS75451

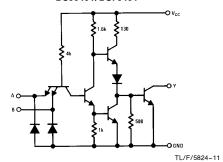
Α	В	Υ
L	L	L (ON State)
L	Н	L (ON State)
Н	L	L (ON State)
H	Н	H (OFF State)

DS55452/DS75452

Α	В	Υ	
L	L	H (OFF State)	
L	Н	H (OFF State)	
Н	L	H (OFF State)	
Н	Н	L (ON State)	

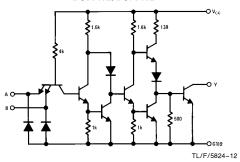
Schematic Diagrams

DS55451/DS75451



Resistor values shown are nominal.

DS55452/DS75452



Resistor values shown are nominal.

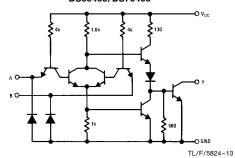
DS55453/DS75453

Α	В	Y
L	L	L (ON State)
L	Н	H (OFF State)
Н	L	H (OFF State)
Н	Н	H (OFF State)

DS55454/DS75454

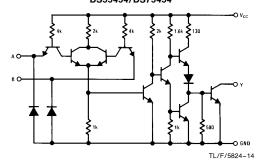
Α	В	Υ
L	L	H (OFF State)
L	Н	L (ON State)
Н	L	L (ON State)
Н	Н	L (ON State)

DS55453/DS75453



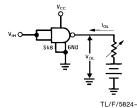
Resistor values shown are nominal.

DS55454/DS75454

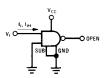


Resistor values shown are nominal.

DC Test Circuits



Both inputs are tested simultaneously. FIGURE 1. V_{IH}, V_{OL}



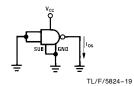
TL/F/5824-18

Each input is tested separately. FIGURE 4. I_I, I_{IH}

TL/F/5824-16

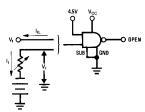
Each input is tested separately.

FIGURE 2. V_{IL}, V_{OH}



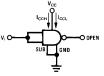
Each input is tested separately.

FIGURE 5. IOS



TL/F/5824-17

Each input is tested separately. FIGURE 3. V_I, I_{IL}



TL/F/5824-20

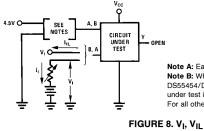
Both gates are tested simultaneously.

FIGURE 6. I_{CCH}, I_{CCL}

V _{IH} O SEE TEST TABLE B	CIRCUIT Y SEE TEST TABLE	V _{OL} I _{OL}
		TL/F/5824-21

	Input	Othor	Other Ou	
Circuit	Under Test	Input	Apply	Measure
DS55451	V _{IH}	V _{IH}	V _{OH}	I _{OH}
	V _{IL}	V _{CC}	l _{OL}	V _{OL}
DS55452	V _{IH}	V _{IH}	l _{OL}	V _{OL}
	V_{IL}	V _{CC}	V _{OH}	I _{OH}
DS55453	V_{IH}	Gnd	V _{OH}	I _{OH}
	V_{IL}	V _{IL}	l _{OL}	V _{OH}
DS55454	V _{IH}	Gnd	I _{OL}	V _{OL}
	V_{IL}	V _{IL}	V _{OH}	I _{OH}

FIGURE 7. V_{IH}, V_{IL}, I_{OH}, V_{OL}



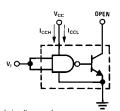
Note A: Each input is tested separately. Note B: When testing DS55453/DS75453, DS55454/DS75454, input not under test is grounded.
For all other circuits it is at 4.5V.

TL/F/5824-22

CIRCUIT UNDER TEST

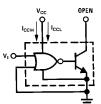
Each input is tested separately. TL/F/5824-23

FIGURE 9. I_I, I_{IH}



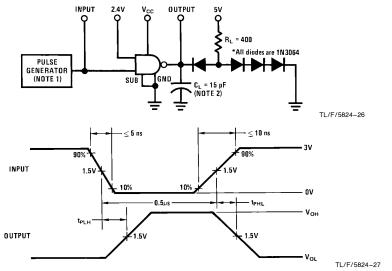
Both gates are tested simultaneously.

FIGURE 10. I_{CCH}, I_{CCL} for AND, NAND Circuits



TL/F/5824-25 FIGURE 11. I_{CCH} , I_{CCL} for OR, NOR Circuits

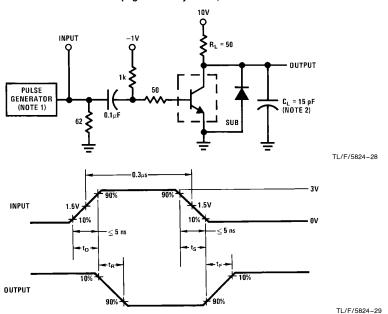
AC Test Circuits and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{OUT} \approx 50\Omega$.

Note 2: C_L includes probe and jig capacitance.

FIGURE 12. Propagation Delay Times, Each Gate



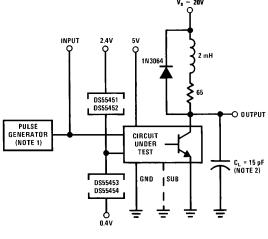
Note 1: The pulse generator has the following characteristics: duty cycle \leq 1%, Z_{OUT} \approx $50\Omega.$

Note 2: C_L includes probe and jig capacitance.

FIGURE 13. Switching Times, Each Transistor

AC Test Circuits and Switching Time Waveforms (Continued) DS55451 DS55452 PULSE GENERATOR (NOTE 1) CIRCUIT Under Test **I** SUB DS55453 DS55454 GND TL/F/5824-30 —≤10 ns \leq 5.0 ns INPUT DS55451 DS55453 1.5V --- ≤ **5.0** ns -3.0V INPUT DS55452 DS55454 1.5V 10% OUTPUT t_{TLH} Note 1: The pulse generator has the following characteristics: PRR = 1.0 MHz, $Z_{OUT} \approx 50\Omega$. TL/F/5824-31 Note 2: C_L includes probe and jig capacitance FIGURE 14. Switching Times of Complete Drivers





TL/F/5824-32

INPUT 90%

DS55451

1.5V

1.5V

1.5V

1.5V

1.5V

0V

40µs

1.5V

0V

0V

0V

0V

0V

0V

0V

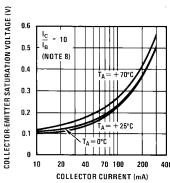
0V

Note 1: The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_{OUT} \approx 50\Omega$.

Note 2: C_L includes probe and jig capacitance.

FIGURE 15. Latch-UP Test of Complete Drivers

Typical Performance Characteristics

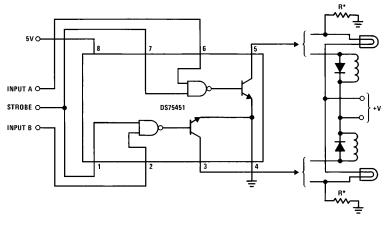


TL/F/5824-37

TL/F/5824-33

FIGURE 16. Transistor Collector-Emitter Saturation Voltage vs Collector Current

Typical Applications



*Optional keep-alive resistors maintain off-state lamp current at $\approx\,$ 10% to reduce surge current.

FIGURE 17. Dual Lamp or Relay Driver

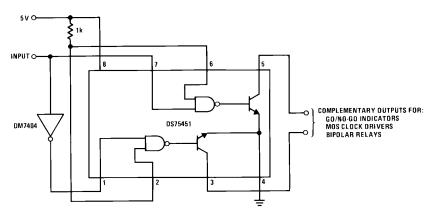
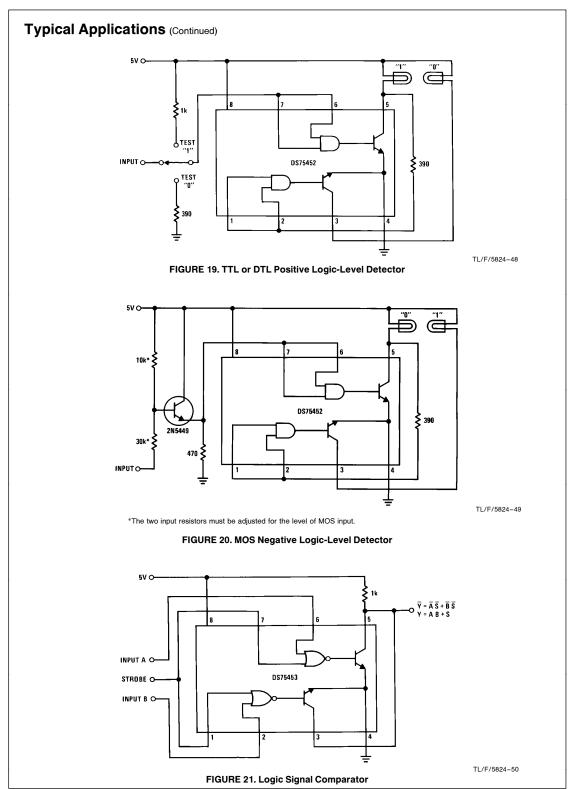


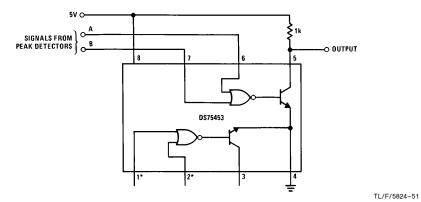
FIGURE 18. Complementary Driver

TL/F/5824-47

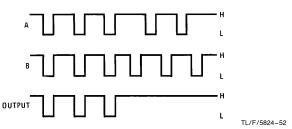
TL/F/5824-46



Typical Applications (Continued)



*If inputs are unused, they should be connected to $\pm 5\mathrm{V}$ through a 1k resistor.



Low output occurs only when inputs are low simultaneously.

FIGURE 22. In-Phase Detector

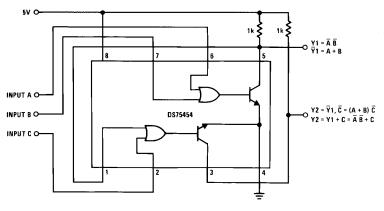
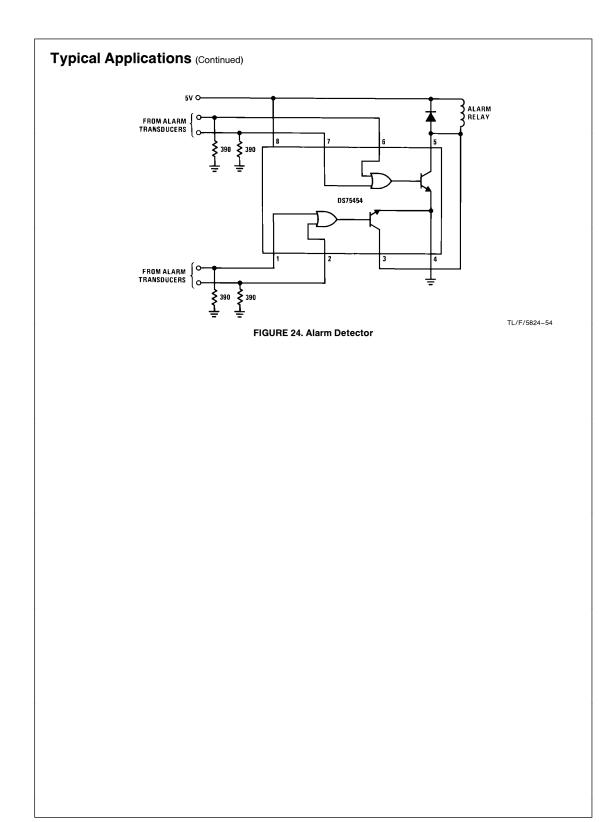
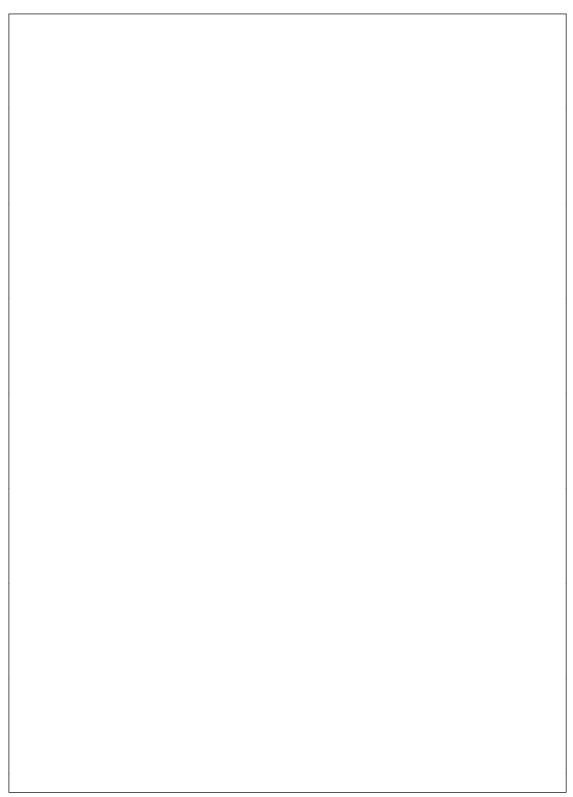
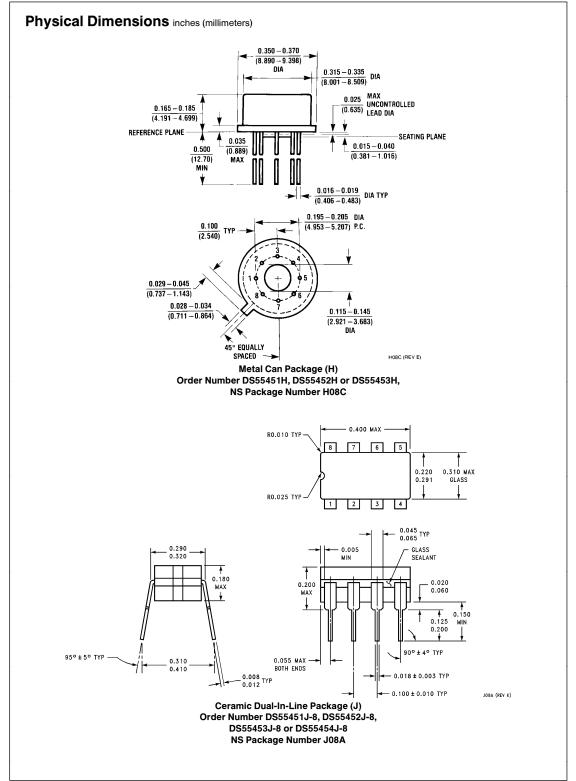


FIGURE 23. Multifunction Logic-Signal Comparator

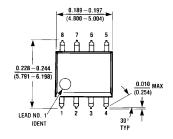
TL/F/5824-53

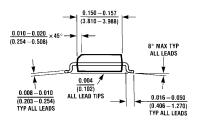


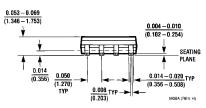




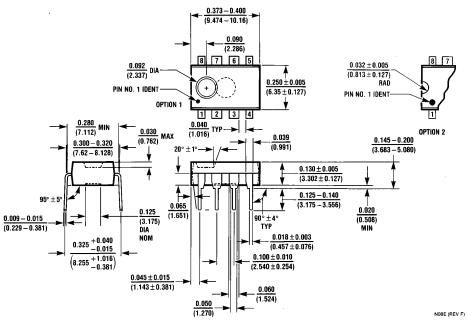
Physical Dimensions inches (millimeters) (Continued)







SO Package (M) Order Number DS75451M, DS75452M, DS75453M or DS75454M NS Package Number M08A



Molded Dual-In-Line Package (N)
Order Number DS75451N, DS75452N, DS75453N, DS75454N
NS Package Number N08E

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- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



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